

Data sheet acquired from Harris Semiconductor SCHS066

### CMOS 8-Bit Addressable Latch

High-Voltage Types (20-Volt Rating)

■ CD4099B 8-bit addressable latch is a serial-input, parallel-output storage register that can perform a variety of functions.

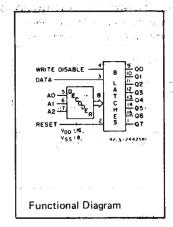
Data are inputted to a particular bit in the latch when that bit is addressed (by means of inputs A0, A1, A2) and when WRITE DISABLE is at a low level. When WRITE DISABLE is high, data entry is inhibited; however, all 8 outputs can be continuously read independent of WRITE DISABLE and address inputs.

A master RESET input is available, which resets all bits to a logic "0" level when RESET and WRITE DISABLE are at a high level. When RESET is at a high level, and WRITE DISABLE is at a low level, the latch acts as a 1-of-8 demultiplexer; the bit that is addressed has an active output which follows the data input; while all unaddressed bits are held to a logic "0" level.

The CD4099B types are supplied in 16-lead hermetic ceramic dual-in-line packages (D and F suffixes), 16-lead plastic dual-in-line packages (E suffix), and in chip form (H suffix).

#### Features:

- Serial data input Active parallel outpu
- Storage register capability Master clear
- Can function as demultiplexer
- Standardized, symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V (full package-temperature range), 100 nA at 18 V and 25°C
- Noise margin (full package-temperature range) = 1 V at V<sub>DD</sub> = 5 V, 2 V at V<sub>DD</sub> = 10 V, 2.5 V at V<sub>DD</sub> = 15 V
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of "B" Series CMOS Devices"



CD4099B Types

### Applications:

- Multi-line decoders
- A/D converters

MAXIMUM RATINGS, Absolute-Maximum Values:	
DC SUPPLY-VOLTAGE RANGE, (VDD)	
Voltages referenced to VSS Terminal)	0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5V to V <sub>DD</sub> +0.5V
DC INPUT CURRENT, ANY ONE INPUT	
POWER DISSIPATION PER PACKAGE (PD):	The state of the s
For T <sub>A</sub> = -55°C to +100°C	500mW
For T <sub>A</sub> = +100°C to +125°C	Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR TA = FULL PACKAGE-TEMPERATURE RANGE (A	Il Package Types) 100mW
OPERATING-TEMPERATURE RANGE (TA)	55°C to +125°C
STORAGE TEMPERATURE RANGE (Tato)	65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	with the second

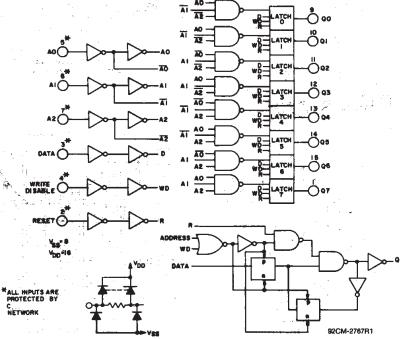
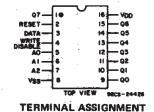


Fig. 1 — Logic diagram of CD4099B and detail of 1 of 8 latches.



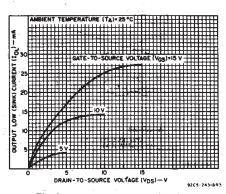


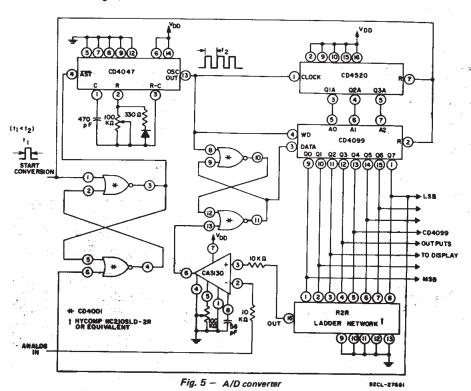
Fig. 2 — Typical output low (sink) current characteristics.

RECOMMENDED OPERATING CONDITIONS at  $T_A = 25^{\circ}$  C (Unless otherwise specified) For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges.

CHARACTERISTIC	SEE	$v_{DD}$	LIN	UNITS		
	FIG. 15*	(V)	MIN.	MAX.	UNITS	
Supply Voltage Range: (At T <sub>A</sub> = Full Package Temperature Range)			3	18	<b>V</b> .	
Minimum Pulse Width, tW		5	200	-		
Data	4	10	100	T		
		15	80		٠.	
		5	400			
Address	8	10	200	-	ns	
		15	125	- ·	-	
		5	150			
Reset	(5)	10	75	_		
		15	50	-		
Setup Time, t <sub>S</sub>		5	100	_		
Data to WRITE DISABLE	(6)	10	50	. –		
		15	35		ns	
Hold Time, tH		5	150			
Data to WRITE DISABLE	7	10	75	· –	ns	
		15	50			

<sup>\*</sup> Circled numbers refer to times indicated on master timing diagram.

Note: In addition to the above characteristics, a WRITE DISABLE ON time (the time that WRITE DISABLE is at a high level) must be observed during an address change for the total time that the external address lines AO, A1, and A2 are settling to a stable level, to prevent a wrong cell from being addressed (see Fig. 3).



MODE SELECTION							
WD	R	ADDRESSED LATCH	UNADDRESSED LATCH				
0	0	Follows Data	Holds Previous State				
0	1	Follows Data   Reset to "0"					
		(Active High 8	-Channel Demulti-   plexer)				
1	0	Holds Previous State					
1	1	Reset to "0"	1				

WD = WRITE DISABLE

R = RESET

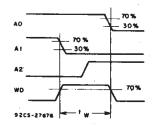


Fig. 3 - Definition of WRITE DISABLE ON time.

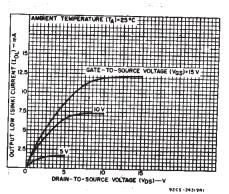


Fig. 4 — Minimum output low (sink) current characteristics.

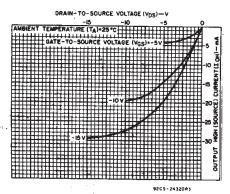
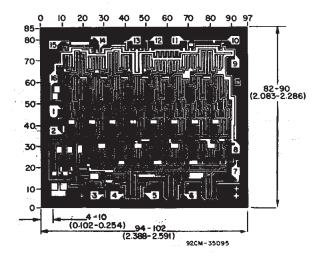


Fig. 6 - Typical output high (source) current characteristics.

### STATIC ELECTRICAL CHARACTERISTICS

CHARACTER-	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)						UNITS			
ISTIC	V <sub>Q</sub> (V)	(S)	V <sub>DD</sub> (V)	_55 _40 +85 +125				+25 Min. Typ. Max.			ONTIS		
Quiescent Device	_	0,5	5	5	5	150	150	<u></u>	0.04	5			
Current,	1 22	0,10	10	10	10	300	300	_	0.04	10	μА		
IDD Max.		0,15	15	20	20	600	600	_	0.04	20			
	-	0,20	20	100	100	3000	3000	-	0.08	100	İ		
Output Low	0.4	0.5	5	0.64	0.61	0.42	0.36	0.51	1				
(Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6				
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	34	6.8	_ = 1			
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	0.36	-0.51	-1	_	mA		
(Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	_			
Current,	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6				
IOH Min.	13.5	0,15	15	-4.2	4	-2.8	-2.4	-3.4	-6.8	_			
Output Voltage:	5	0,5	5	0.05			-	0	0.05				
Low-Level,	·	0,10	10	0.05				_	0	0.05	v		
VOL Max.	-	0,15	15	0.05			=	0	0.05				
Output Voltage:	- 1	0,5	5	4.95			4.95	5	-	ľ			
High-Level,	-	0,10	10	9.95				9.95	10		.		
VOH Min.	_	0,15	15	14.95				14.95	15	=2"			
Input Low	0.5, 4.5	-	5	1.5				_		1.5	•		
Voltage,	1, 9	-	10	3				_	_	3			
Vil Max.	1.5,13.5	-	15	4				-	_	4	l v l		
Input High	0.5, 4.5	-	5	3.5			3.5	_	-	*			
Voltage,	1, 9	_	10	7				7			]		
VIH Min.	1.5,13.5	_	15			11		11		_			
Input Current IIN Max.	_ '	0,18	18	±0.1	±0.1	,±1	±1	-	±10-5	±0.1	μΑ		



## CD4099BH DIMENSIONS AND PAD LAYOUT

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10<sup>-3</sup> inch).

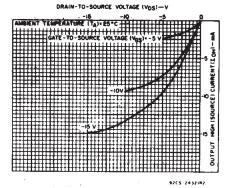


Fig.7 - Minimum output high (source) current characteristics.

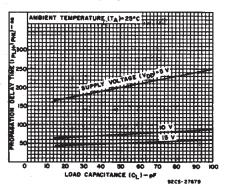


Fig. 8 — Typical propagation delay time (data to Qn) vs. load capacitance.

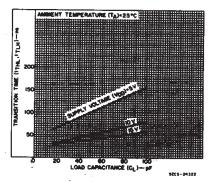


Fig. 9 — Typical transition time vs. load capacitance.

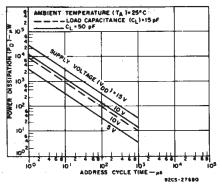


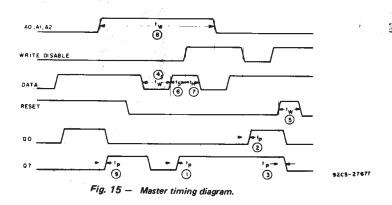
Fig. 10 — Typical dynamic power dissipation vs. address cycle time.

### CD4099B Types

# DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A$ = 25° C, $C_L$ = 50 pF, Input $t_F$ , $t_f$ = 20 ns, $R_L$ = 200 K $\Omega$

CHARACTERISTIC	SEE	CONDITIONS SEE V <sub>DD</sub> FIG.15* (V)		LIMITS ALL PACKAGE TYPES TYP. MAX.		
Propagation Delay: tpLH		5	200	400		
<sup>†</sup> PHL		10	75	150		
Data to Output,		15	50	100		
WRITE DISABLE		5	200	400		
to Output, tpLH	. 2	10	80	160	ns	
tPHL	-	15	60	120		
	<del></del>	5	175	350		
Reset to Output,	3	10	80	160		
tpht		15	65	130		
Address to Output,		5	225	450		
tPLH		10	100	200		
tРНL		15	75	150		
Transition Time, t <sub>THL</sub>		5	100	200	<del></del> .	
(Any Output) t <sub>TLH</sub>	1 1	10	50	100	ns	
		15	40	80		
Minimum Pulse		5	100	200		
Width, t <sub>W</sub>	4	10	50	100	ns	
Data		15	40	80	****	
		5	200	400		
Address	(8)	10	100	200	ns	
		15	65	125	113	
		5	75	150		
Reset	(5)	10	40	75	ns	
-		15	25	50	•••	
Minimum Setup		5	50	100	·	
Time, t <sub>S</sub>	6	10	25	50	ns	
Data to WRITE DISABLE		15	20	35	•	
Minimum Hold		5	75	150		
Time, t <sub>H</sub>	0	10	40	75	ns	
Data to WRITE DISABLE		15	25	50		
Input Capacitance, CIN	Any Inp	ut	5	7.5	pF	

<sup>\*</sup>Circled numbers refer to times indicated on master timing diagram.



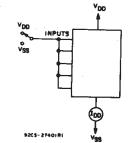


Fig. 11 — Quiescent device current test circuit.

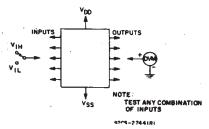


Fig. 12 - Input voltage test circuit.

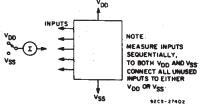


Fig. 13 - Input current test circuit.

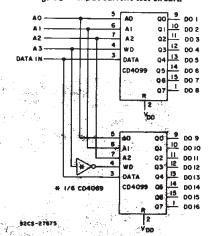
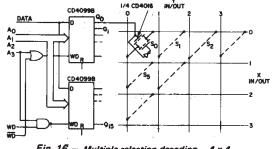


Fig. 14 - 1 of 16 decoder/demutsielexer.



### **IMPORTANT NOTICE**

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1998, Texas Instruments Incorporated